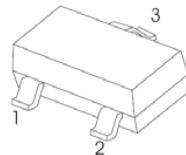


FEATURES

- $V_{DS}(V) = -30V$
- $R_{DS(ON)} < 46m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 54m\Omega$ ($V_{GS} = -4.5V$)

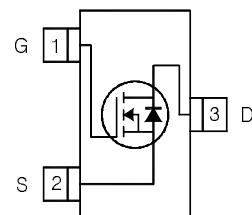
SOT - 23



1. GATE
2. SOURCE
3. DRAIN

APPLICATIONS

- For Mobile Computing
- Load Switch
- Notebook Adaptor Switch
- DC/DC Converter



AB SOLUTEMA XIMUM RATINGS ($T_A = 25^\circ C$, unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|----------------------|------|
| Drain-Source Voltage | V_{DS} | - 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150^\circ C$) | I_D | - 5.6 | A |
| | | - 5.1 | |
| | | - 5.4 ^{b,c} | |
| | | - 4.3 ^{b,c} | |
| Pulsed Drain Current ($t = 100 \mu s$) | I_{DM} | - 18 | W |
| Continous Source-Drain Diode Current | I_S | - 2.1 | |
| | | - 1 ^{b,c} | |
| Maximum Power Dissipation | P_D | 2.5 | |
| | | 1.6 | |
| | | 1.25 ^{b,c} | |
| | | 0.8 ^{b,c} | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|--|--------------|------------|---------|------|
| Maximum Junction-to-Ambient ^{b,d} | R_{thJA} | 75 | 100 | °C/W |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 40 | |

Notes:

- a. Based on $T_C = 25^\circ C$.
- b. Surface mounted on 1" x 1" FR4 board.
- c. $t = 5 s$.
- d. Maximum under steady state conditions is 166 °C/W.

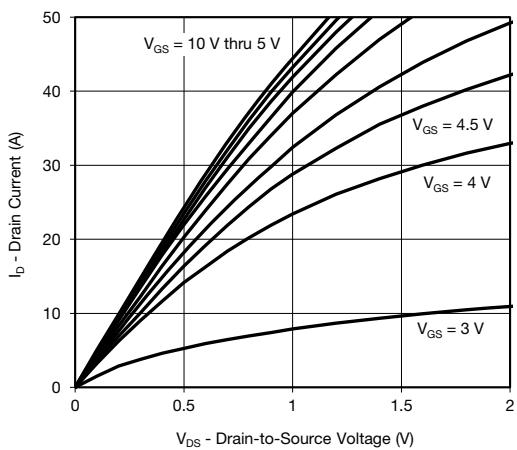
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | |
|---|--------------------------------|--|---------------------|------|-----------|---------------|---|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$ | -30 | | | V | |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = -250 \mu\text{A}$ | | -19 | | mV/°C | |
| $V_{GS(\text{th})}$ Temperature Coefficient | $\Delta V_{GS(\text{th})}/T_J$ | | | 4 | | | |
| Gate-Source Threshold Voltage | $V_{GS(\text{th})}$ | $V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ | -0.5 | | -2.0 | V | |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ | | -1 | | μA | |
| | | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$ | | | -5 | | |
| On-State Drain Current ^a | $I_{D(\text{on})}$ | $V_{DS} \leq -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -2.5 | | | A | |
| Drain-Source On-State Resistance ^a | $R_{DS(\text{on})}$ | $V_{GS} = -10 \text{ V}, I_D = -4.4 \text{ A}$ | | 46 | 55 | mΩ | |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$ | | 54 | 63 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -15 \text{ V}, I_D = -3.4 \text{ A}$ | | 18 | | S | |
| Dynamic^b | | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 1295 | | pF | |
| Output Capacitance | C_{oss} | | | 150 | | | |
| Reverse Transfer Capacitance | C_{rss} | | | 130 | | | |
| Total Gate Charge | Q_g | $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -5.4 \text{ A}$ | | 24 | 36 | nC | |
| Gate-Source Charge | Q_{gs} | | | 11.4 | 17 | | |
| Gate-Drain Charge | Q_{gd} | | | 3.4 | | | |
| Gate Resistance | R_g | | $f = 1 \text{ MHz}$ | 3.8 | | | |
| Turn-On Delay Time | $t_{d(\text{on})}$ | $V_{DD} = -15 \text{ V}, R_L = 3.5 \Omega$ $I_D \approx -4.3 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$ | | 1.5 | 7.7 | 15.4 | Ω |
| Rise Time | t_r | | | 13 | 20 | ns | |
| Turn-Off Delay Time | $t_{d(\text{off})}$ | | | 4 | 8 | | |
| Fall Time | t_f | | | 38 | 57 | | |
| Turn-On Delay Time | $t_{d(\text{on})}$ | | | 6 | 12 | | |
| Rise Time | t_r | $V_{DD} = -15 \text{ V}, R_L = 3.5 \Omega$ $I_D \approx -4.3 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$ | | 28 | 42 | ns | |
| Turn-Off Delay Time | $t_{d(\text{off})}$ | | | 16 | 24 | | |
| Fall Time | t_f | | | 30 | 45 | | |
| | | | | 10 | 20 | | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25^\circ\text{C}$ | | | -2.1 | A | |
| Pulse Diode Forward Current ($t = 100 \mu\text{s}$) | I_{SM} | | | | -80 | | |
| Body Diode Voltage | V_{SD} | $I_S = -4.3 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.8 | -1.2 | V | |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = -4.3 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$ | | 15 | 23 | ns | |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 7 | 14 | nC | |
| Reverse Recovery Fall Time | t_a | | | 8 | | ns | |
| Reverse Recovery Rise Time | t_b | | | 7 | | | |

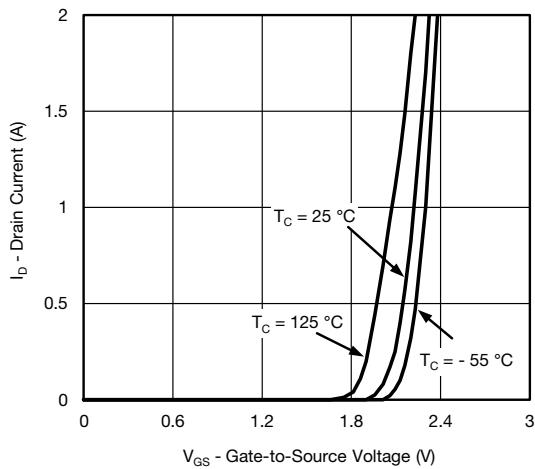
Notes:

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

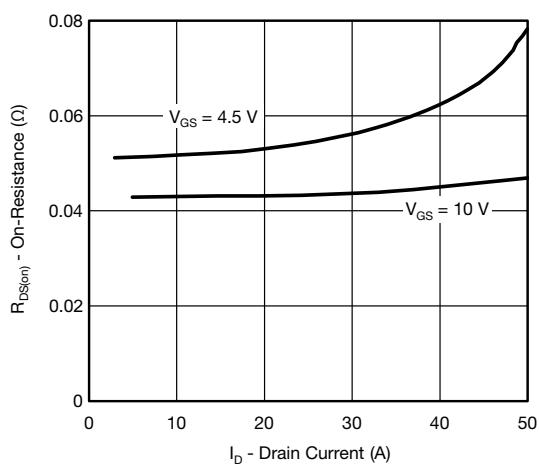
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



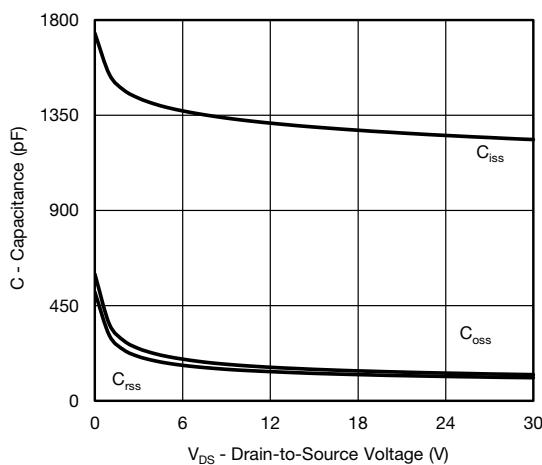
Output Characteristics



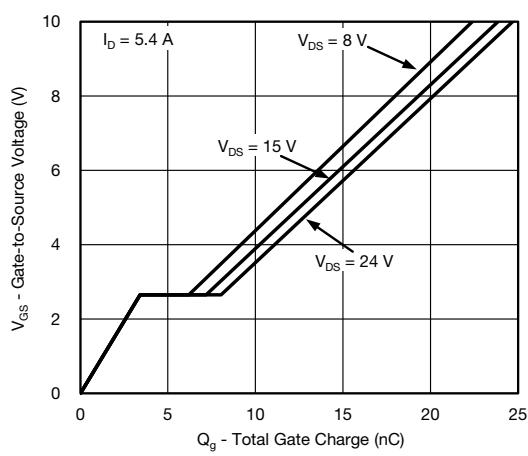
Transfer Characteristics



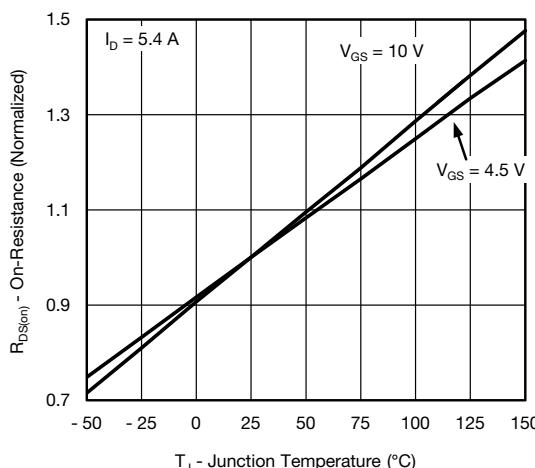
On-Resistance vs. Drain Current



Capacitance

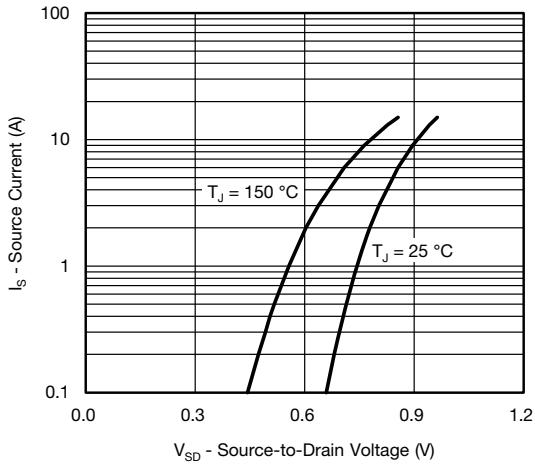


Gate Charge

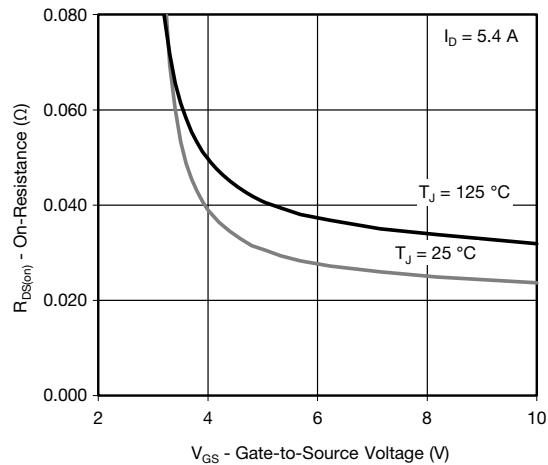


On-Resistance vs. Junction Temperature

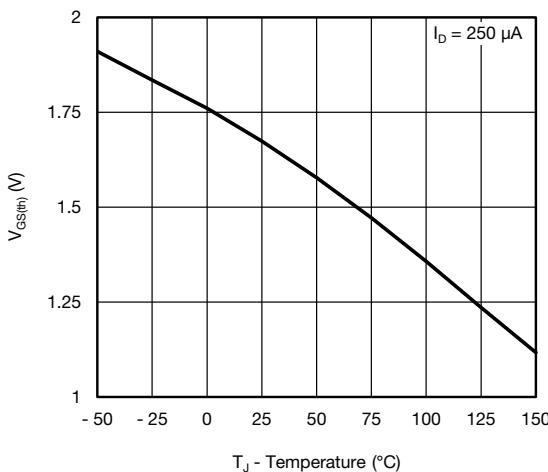
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



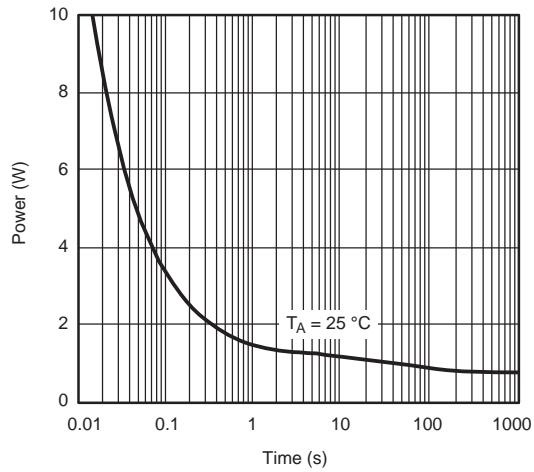
Source-Drain Diode Forward Voltage



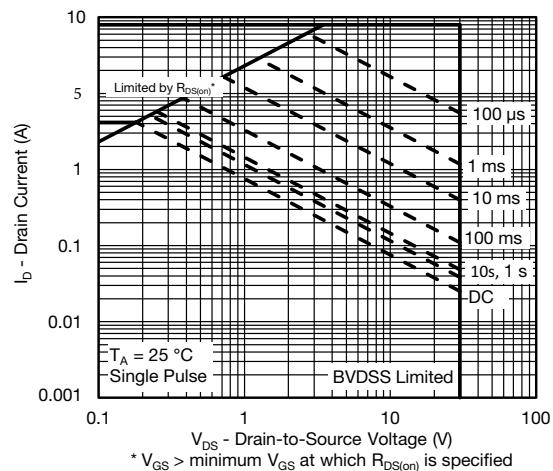
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

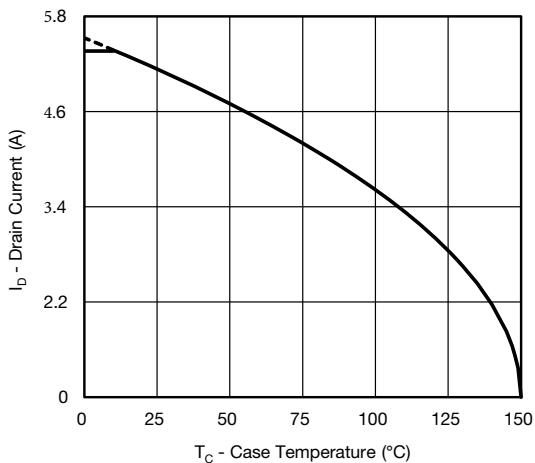


Single Pulse Power (Junction-to-Ambient)

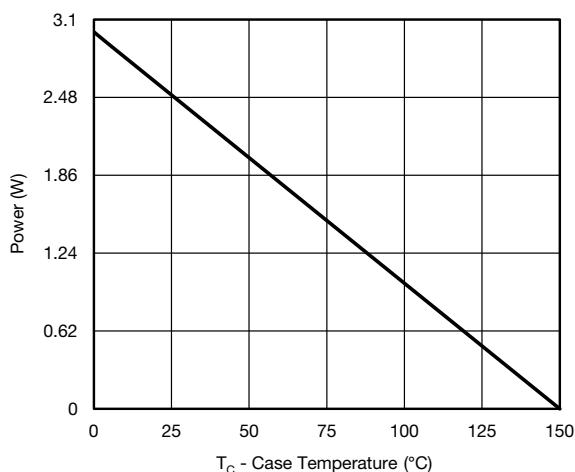


Safe Operating Area, Junction-to-Ambient

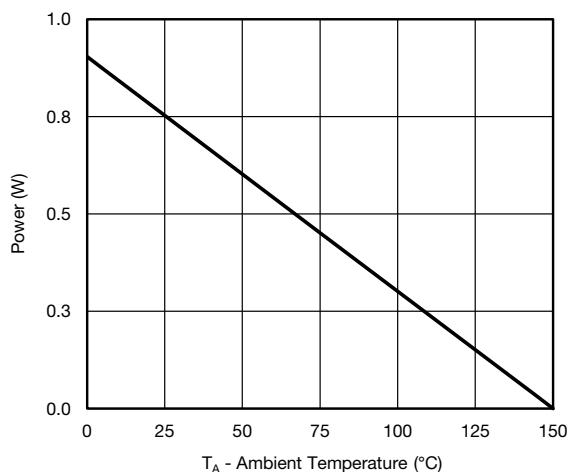
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



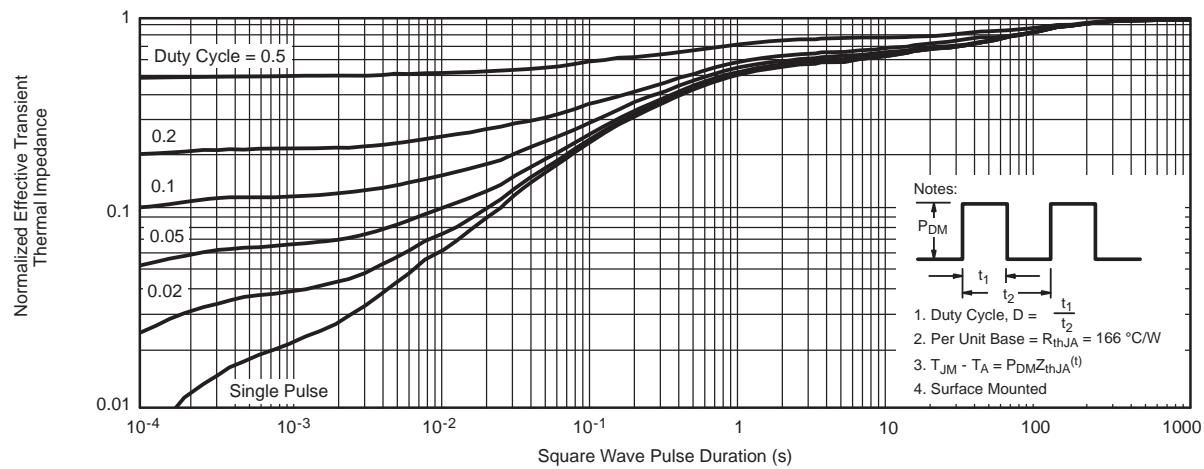
Power, Junction-to-Foot



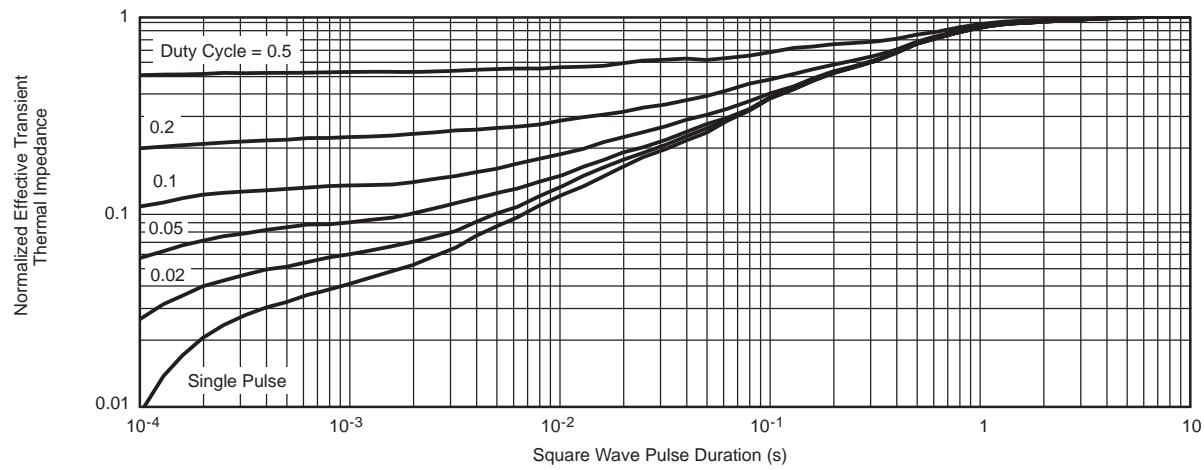
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(\max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

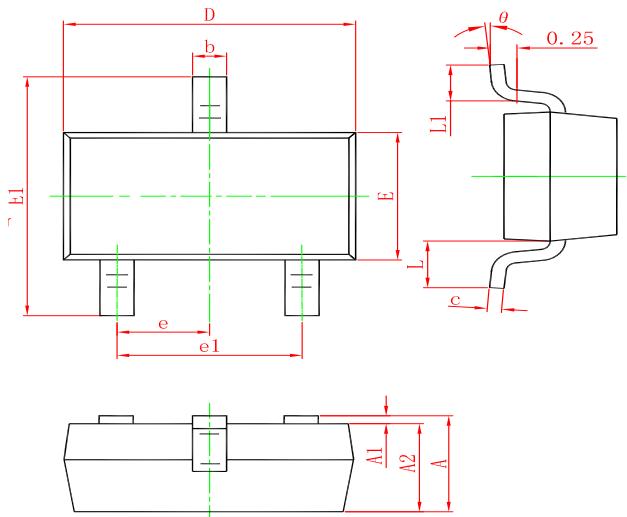


Normalized Thermal Transient Impedance, Junction-to-Ambient



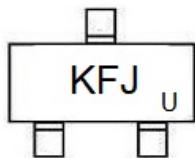
Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-23 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP. | | 0.037 TYP. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF. | | 0.022 REF. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

Marking



Ordering information

| Order code | Package | Baseqty | Deliverymode |
|------------|---------|---------|---------------|
| SSM3J332R | SOT-23 | 3000 | Tape and reel |